

*B1
Cancel*

after treating the conductive liner with hydrogen, filling said hole with a conductive metal.

Cancel Claim 2.

Amend claim 9 to read as follows:

9. (amended) A method for forming a contact in an integrated circuit, comprising the steps of:

D2
forming a dielectric layer over a semiconductor body;
etching a contact hole extending through said dielectric layer;
depositing titanium over said dielectric layer, including on exposed surfaces within said contact hole;
annealing said titanium;
treating said titanium with hydrogen;
depositing TiN over said titanium; and
then, filling said contact hole with tungsten.
